100 V

30 A

0.78 V



advanced

# Schottky Diode Gen<sup>2</sup>

High Performance Schottky Diode Low Loss and Soft Recovery Single Diode

Part number

**DSA 30 I 100 PA** 



# 1

Backside: cathode

# Features / Advantages:

- Very low Vf
- Extremely low switching losses
- low Irm values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

# **Applications:**

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

# Package:

 $V_{RRM} =$ 

 $I_{FAV} =$ 

- Housing: TO-220
- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

### Ratings

Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RRM}$	max. repetitive reverse voltage		$T_{VJ} = 25^{\circ}C$			100	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 100 V	$T_{VJ} = 25^{\circ}C$			0.9	mA
		V <sub>R</sub> = 100 V	$T_{VJ} = 125$ °C			5	mA
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A	$T_{VJ} = 25^{\circ}C$			0.95	V
		$I_F = 60 A$				1.15	V
		I <sub>F</sub> = 30 A	$T_{VJ} = 125$ °C			0.78	V
		$I_F = 60 A$				1.01	V
I <sub>FAV</sub>	average forward current	rectangular d = 0.5	$T_{c} = 150$ °C			30	Α
V <sub>F0</sub>	threshold voltage slope resistance $ T_{VJ} = 17 $		T <sub>VJ</sub> = 175°C			0.46	V
$\mathbf{r}_{F}$						7.8	mΩ
R <sub>thJC</sub>	thermal resistance junction to case					0.85	K/W
T <sub>VJ</sub>	virtual junction temperature			-55		175	°C
P <sub>tot</sub>	total power dissipation		$T_c = 25^{\circ}C$			175	W
I <sub>FSM</sub>	max. forward surge current	t = 10 ms (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			230	Α
C¹	junction capacitance	$V_R = 12V$ ; $f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		289		pF
E <sub>AS</sub>	non-repetitive avalanche energy	$I_{AS} = 10 \text{ A}; L = 100 \mu\text{H}$	$T_{VJ} = 25^{\circ}C$			5	mJ
I <sub>AR</sub>	repetitive avalanche current	$V_A = 1.5 \cdot V_R \text{ typ.: } f = 10 \text{ kHz}$				1	Α

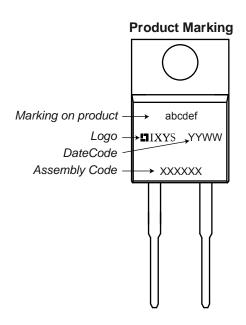




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				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I <sub>RMS</sub>	RMS current	per pin <sup>1)</sup>			35	Α	
R <sub>thCH</sub>	thermal resistance case to heats	sink		0.50		K/W	
T <sub>stg</sub>	storage temperature		-55		150	°C	
Weight				2		g	
M <sub>D</sub>	mounting torque		0.4		0.8	Nm	
F <sub>c</sub>	mounting force with clip		20		60	N	

<sup>1)</sup> I<sub>RMS</sub> is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip. In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.



#### Part number

D = Diode

S = Schottky Diode

A = low VF

30 = Current Rating [A]

I = Single Diode

100 = Reverse Voltage [V]

PA = TO-220AC (2)

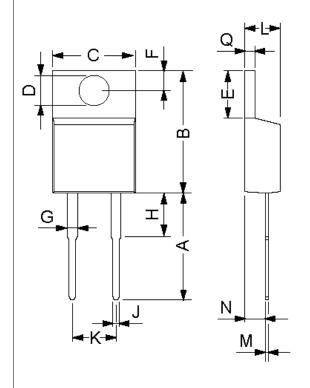
Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	DSA 30 I 100 PA	DSA30I100PA	Tube	50	504162





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# Outlines TO-220



Dim.	Millimeter		Inches		
Dilli.	Min.	Max.	Min.	Max.	
Α	12.7	14.73	0.5	0.58	
В	14.23	16.51	0.56	0.65	
С	9.66	10.66	0.38	0.42	
D	3.54	4.08	0.139	0.161	
E	5.85	6.85	2.3	0.42	
F	2.54	3.42	0.1	0.135	
G	1.15	1.77	0.045	0.07	
Н	-	6.35	-	0.25	
J	0.64	0.89	0.025	0.035	
K	4.83	5.33	0.19	0.21	
L	3.56	4.82	0.14	0.19	
М	0.51	0.76	0.02	0.03	
N	2.04	2.49	0.08	0.115	
Q	0.64	1.39	0.025	0.055	